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Publication List

Atsushi Oshiyama

(A) Original Papers

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6. A. Oshiyama, “Microscopic Theory of Oxidation of Si and Formation of Si/SiO_2 Interface”, *Int. Workshop on Computational Materials Science,* Tsukuba (1990).

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8. 斎藤晋, 押山淳, “Electronic Structure and Superconductivity of Alkali-doped C_{60}”, 日本物理学会 (北海道大学, 1991).

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10. A. Oshiyama, Y. Miyamoto and M. Hane, "Microscopic Calculation for the Initial Stage of Silicon Oxidation", International Workshop on Science and Technology for Surface reaction Process (Takehashi, Tokyo, 1992).

11. 押山淳, "Microscopic Mechanisms of Atomic Diffusion in Si under Pressure", 日本物理学会 (慶應大学, 1992).

12. 押山淳, "Mechanisms and Controle of Impurity Diffusion in Si", 応用物理学会学術講演会 (日本大学, 1992).

13. 押山淳, "Microscopic Theory of Initial Stage of Silicon Oxidation", 応用物理学会学術講演会 (日本大学, 1992).

14. S. Saito and A. Oshiyama, "Electronic Structure and Supeconductivity of Fullerenes and Fullerides", *181st Electrochemical Society Meeting* (St Louise, 1992).

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16. (**Plenary**) S. Saito, A. Oshiyama, Y. Miyamoto, N. Hamada and S. Sawada, "Cohesion, Electron States and Superconductivity of Fullerenes and Fullerides", *21st Int. Conf. Physics of Semiconductors* (Beijing, 1992).

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20. A. Oshiyama, "C_{60} as a Superatom: Electronic Structure of Doped Fullerides", *182nd Electrochemical Society Meeting* (Tronto, 1992).

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42. A. Oshiyama, “Prediction of Electronic Properties of Carbon-Based Nanostructures” Tsukuba Symposium on Carbon Nanotube (Tsukuba, October 2001).

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52. 押山淳, 「ナノ・バイオ物質における密度汎関数法計算」 計算科学の基盤技術とその発展：RIMS 研究集会（2005 年 12 月、京都大学）

53. 押山淳,「ナノ・バイオ物質での密度汎関数法計算：現象の微視的機構と予測」ナノ学会第４回大会 （2006 年 5 月，京都大学）

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55. A. Oshiyama, “Atomic and Electronic Structures of Carbon nanotubes on Si and Metal Surfaces” 9th Asian Workshop on First-Principles Electronic-Structure Calculations (Seoul, November, 2006).

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57. 押山淳、“密度汎関数理論によるナノ・バイオ計算”, Supercomputer Workshop 2007 計算分子科学の 30 年と将来、（自然科学研究機構, 2007 年 2 月）

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60. A. Oshiyama, “Density-Functional Approach to Nano- and Bio-Materials” ICYS(NIMS)-ICMR(UC Santa Barbara) Summer School on Nanomaterials (Tsukuba, July 23-28, 2007)

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62. A. Oshiyama, “Large-scale Density-Functional Calculations using Real-Space Parallel-Computation Technique”, 1st Int. Conf. of The Grand Challenge to Next-Generation Integrated Nanoscience (June 3 - 7, 2008, Tokyo)

63. Y. Fujimoto, T. Korestune, S. Saito, T. Miyake, and A. Oshiyama, “Structural and electronic properties of new crystalline phase of Si and Ge”, International Conference on Quantum Simulatiors and Design, (2008/6/2, Tokyo)

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65. A. Oshiyama, “Real-Space Density-Functional-Theory Scheme and its Application to Large Systems”, Supercomputing in Solid State Physics, (February 16 -1 9, 2009, Kashiwa, Chiba).

66. 押山淳, “ナノ構造体の面白さ - 電子論による機能探索” 第 56 会応用物理学関係連合講演会シンポジウム「ポストスケーリング時代をデバイス・物性物理から斬る ー これが半導体デバイスの未来像だー」(2009 年 3 月、筑波大学)

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68. A. Oshiyama, “Large-Scale Density-Functional Calculations for Atomic and Electronic Structures of Si Nanowires” PICE International Symposium on Silicon Nano Devices in 2030: Prospects by World’s Leading Scientists (October 13-14, 2009, Tokyo, Japan).

69. A. Oshiyama, “Large-Scale Density Functional Calculations for Silicon and Carbon Nanostructures”, Conference on Computaional Physics 2009 (Kaoshing, Taiwan, December 15 - 19, 2009)

70. A. Oshiyama, “Large-Scale Density Functional Calculations in Real Space Scheme”, Int. Workshop on Computational Physics and Materials Sciences: total energy and force method (Shanghai, January 7 - 9, 2010)

71. A. Oshiyama, “Current Status of Density-Functional-Theory-Based Calculations for Nano- and Bio-Materials”, Int. Sympo. “Nanoscience and Quantum Physics 2011” (Tokyo, January 26-28, 2011).

72. 押山淳, “励起ナノプロセス入門 - 第一原理計算” 第 48 回応用物理学会スクール (2011 年 8 月 29 日、山形大学)

73. 押山淳, “PACS-CS における物性物理学研究” 第 2 回「学際計算科学による新たな知の発見・統合・創出」シンポジウム　(2011 年 9 月 1 日、筑波大学)

74. 押山淳, “コンピューティクスによる物質デザイン : RSDFT を例として” 東京大学物性研究所計算物質科学研究センター第 1 回シンポジウム　(2011 年 9 月 12-13 日、東京大学)

75. A. Oshiyama, “Materials Design through Computics: nanowires and Nanotubes” Inernational Focus Workshop on Quantum Simulations and Design (September 27, 2011, Dresden, Germany)

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